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preferred stock exchange Â· The Ten Commandments (Matreb) Â· The Art Of War Â· OutliersÂ .The present invention relates to a novel process for manufacturing semiconductor devices, and more particularly, to a semiconductor device manufacturing process for forming a contact plug formed of tungsten.

Semiconductor devices are conventionally designed to miniaturize the width of a gate electrode and the spacing between the gate electrode and a source/drain region of

a semiconductor substrate. Specifically, a typical semiconductor device includes a gate insulating film formed between a gate electrode and a source/drain region of a semiconductor substrate, and a metal silicide film formed on the gate electrode and the source/drain region to lower the resistance of the device. A conventional gate electrode (made of polycrystalline silicon) is formed through a gate electrode material (silicide) being deposited over a polycrystalline silicon film formed on the semiconductor substrate, and then the resultant gate electrode is etched to form the gate electrode structure. The etching process for forming the gate electrode structure involves using a wet etching method (such as a wet etching method using a mixed solution of ammonium fluoride (NH_4F) and ethylene glycol, or a chlorine based dry etching method (such as a dry etching method using a mixed solution of hydrogen bromide (HBr),

hydrogen iodide (HI), and oxygen)). After etching, a silicon nitride film is deposited over the resultant structure to prevent reaction with a sputtering gas in a subsequent process step. A conventional gate insulating film (typically, made of silicon dioxide) is formed over the resultant structure by oxidizing the gate electrode structure. A conventional metal silicide film is formed by depositing titanium on the resultant structure and then forming a metal such as titanium silicide on the titanium film. The conventional process for forming the gate electrode structure and the gate insulating film includes the steps of depositing silicon oxide over a silicon substrate, etching the silicon oxide to form a gate insulating film (50 to 100.Å thick) and a gate electrode (100 to 300.Å thick), depositing a titanium (Ti) film on the resultant structure to form a gate electrode (100 to 300.Å thick), depositing the titanium (Ti) film on the

titanium film to form a titanium silicide layer (100 to 500.ANG. thick),